

6501130 NATL SEMICOND, (DISCRETE)

28C 35432 D

T-29-29



DARLINGTON

Type No.	Case Style	VCBO (V) Min	VCEO (V) Min	VEBO (V) Min	ICES* ICBO (μA) Max	VCB (V) @	hFE Min Max	IC @ (mA) VCE (V)	VCE(SAT) (V) Max	VBE(SAT) (V) Min Max	IC (mA) @	Cob (pF) Max	fT (MHz) Min Max	e IC (mA)	Process No.
2N5305	TO-92 (94)				0.1	25	2000 20,000	2 5	1.4		200	10	60	2	05
2N5306	TO-92 (94)				0.1	25	7000 70,000	2 5	1.4		200	10	60	2	05
2N5307	TO-92 (94)				0.1	40	2000 20,000	2 5	1.4		200	10	60	2	05
2N5308	TO-92 (94)				0.1	40	7000 70,000	2 5	1.4		200	10	60	2	05
2N6426	TO-92 (92)	40	40	12	0.05	30	20,000 200,000 30,000 300,000	10 5 100 5	1.2		50	7	150	10	05
2N6427	TO-92 (92)	40	40	12	0.05	30	10,000 100,000 20,000 200,000	10 5 100 5	1.2	2	50	7	130	10	05
2N6548	TO-202 (55)	50	40	12	0.1	30	14,000 140,000 25,000 150,000	50 5 200 5	1.5	2	500	7	1	200	05
2N6549	TO-202 (55)	50	40	12	0.1	30	15,000 150,000 10,000 500 5	200 5 500 5				7	1	200	05
2N6724	TO-126	50		12			25,000 200 5 15,000 500 5	200 5 500 5	1.0		200		1	10 200	05
2N6725	TO-126	60		12	0.1	40	4000 40,000	1A 5	1.0		200		1	10 200	05
92PU45	TO-237 (91)	50		12	0.1	30	4000 15,000 25,000	1A 5 500 5	1.5	2.0	1A		100	200	05
92PU45A	TO-237 (91)	60		12	0.1	40	4000 15,000 25,000	1A 5 500 5	1.0		200		100	200	05
D40C1	TO-202 (55)		30		0.5*	30	10,000 60,000	200 5	1.5	2.0	500	10			05
D40C2	TO-202 (55)		30		0.5*	30	40,000	200 5	1.5	2.0	500	10			05
D40C3	TO-202 (55)		30		0.5*	30	90,000	200 5	1.5	2.0	500	10			05
D40C4	TO-202 (55)		40		0.5*	40	10,000 60,000	200 5	1.5	2.0	500	10			05

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Type No.	Case Style	V _{CB0} (V) Min	V _{CE0} (V) Min	V _{EB0} (V) Min	I _{CB0} (μA) Max	V _{CB} (V)	I _{FE} Min	I _C @ V _{CE} (mA)	V _{CE(SAT)} (V) Max	V _{BE(SAT)} (V) Min	I _C (mA) Max	C _{ob} (pF) Max	f _T (MHz) Min	Process No.
D40C5	TO-202 (55)		40		0.5*	40	40,000	200	1.5	2.0	500	10		05
D40C7	TO-202 (55)		50		0.5*	50	10,000	200	1.5	2.0	500	10		05
D40C8	TO-202 (55)		50		0.5*	5	40,000	200	1.5	2.0	500	10		05
D40K1	TO-202 (55)		30				10,000	200				10		05
							1000	1.5A						
							1000	1A						
D40K2	TO-202 (55)		50				10,000	200						05
							1000	1.5A						
							1000	1A						
D40K3	TO-202 (55)		30				10,000	200						05
							1000	1.5A						
							1000	1A						
D40K4	TO-202 (55)		50				10,000	200						05
							1000	1.5A						
							1000	1A						
MPSA12	TO-92 (92)	20			0.1	15	20,000	10	1.0		10			05
MPSA13	TO-92 (92)	30			0.1	30	10,000	100	1.5		100		125	05
							5000	10						
MPSA14	TO-92 (92)	30			0.1	30	20,000	100	1.5		100		125	05
							10,000	10						
NSD151	TO-202 (55)		30	12			5000	10	1.5		100	8	5	05
							10,000	150,000						
NSD152	TO-202 (55)			12			5000	10	1.5		100	8	5	05
							10,000	25,000						
NSD153	TO-202 (55)			12			20,000	10	1.5		100	8	5	05
							5000	100						
NSD154	TO-202 (55)			12			20,000	10	1.5		100	8	5	05
							5000	100						
NSDU45	TO-202 (55)	50		12			25,000	200	1.0		200	8	1	05
							15,000	500						
							4000	1A						
NSDU45A	TO-202 (55)	60		12	0.1	10	25,000	200	1.0		200	8	1	05
							15,000	500						
							4000	1A						

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Type No.	Case Style	V _{CB0} (V) Min	V _{CE0} (V) Min	V _{EB0} (V) Min	I _{CS*} I _{CB0} (μA) Max	V _{CB} (V) e	h _{FE}		V _{CE(SAT)} & V _{BE(SAT)} (V)		I _C (mA) e	C _{ob} (pF) Max	f _T (MHz)		Process No.
							Min	Max	Max	Min			Min	Max	
2N6037	TO-126		40		500	40	100 750 500	4A 2A 0.5	2.0 3.0	4.0	2A 4A	200	25		4J
2N6038	TO-126		60		500	60	100 750 500	4A 2A 0.5	2.0	4.0	2A 4A	200	25		4J
2N6039	TO-126		80		500	80	100 750 500	4A 2A 0.5	2.0	4.0	2A 4A	200	25		4J
2N6386	TO-220		40		300*	40	100 1000 20,000	8 3 3	2.0 3.0		3 8	200	20	1	4J
MJE800	TO-126		60		200	60	750	1.5	2.5		1.5				4J
MJE801	TO-126		60		200	60	750	2	2.8		2				4J
MJE802	TO-126		80		200	80	750	1.5	2.5		1.5				4J
MJE803	TO-126		80		200	80	750	2	2.8		2				4J
TIP110	TO-220		60		1 mA	60	500 1000	2 1	2.5		2				4J
TIP111	TO-220		80		1 mA	80	500 1000	2 1	2.5		2				4J
TIP112	TO-220		100		1 mA	100	500 1000	2 1	2.5		2				4J
TIP120	TO-220		60		200	60	1000 1000	3 0.5	2.0 4.0		3 5				4J
TIP121	TO-220		80		200	80	1000 1000	3 0.5	2.0 4.0		3 5				4J
TIP122	TO-220		100		200	100	1000 1000	3 3	2.0 2.0		3 3				4J
2N6387	TO-220	60	60	5			1000 1000	5 10	3.0		10	200			4K
2N6388	TO-220	80	80	5			1000 1000	5 10	3.0		10	200			4K
2N6043	TO-220		60		500	60	10,000 1000	4 8	2.0 4.0	4.5	4 8	200	4	3	4K
2N6044	TO-220		80		500	80	1000 1000	4 8	2.0 4.0	4.5	4 8	200	4	3	4K
2N6045	TO-220		100		500	100	1000 1000	4 8	2.0 4.0	4.5	4 8	200	4	3	4K
SE9300	TO-220		60	4			750 1000 100	1 4 7.5	3 3 3						4K

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Type No.	Case Style	VCBO (V) Min	VCEO (V) Min	VEBO (V) Min	ICES* ICBO (μA) Max	VCB (V)	hFE		VCE(SAT) (V)		Cob (pF) Max	fT (MHz) Min Max	IC (mA) @	Process No.	
							Min	Max	Max	Min					
SE9301	TO-220		80	4				1	3					4K	
								1000	4						3
								100	7.5						3
SE9302	TO-220		100	4				1	3					4K	
								1000	4						3
								100	7.5						3
TIP100	TO-220	60			50	40	20,000	3	4	2.0				4K	
TIP101	TO-220	80			50	60	20,000	3	4	2.0				4K	
TIP102	TO-220	100			50	80	20,000	3	4	2.0				4K	
TIP130	TO-220		60		200	60	15,000	4	4	2.0				4K	
TIP131	TO-220		80		200	60	15,000	4	4	2.0				4K	
TIP132	TO-220		100		200	100	15,000	4	4	2.0				4K	

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